



LT1008P

USB TypeC PD2.0/PD3.0, QC3.0/QC2.0, FCP, SCP, AFC, Apple 2.4A, BC1.2, MTK PE+ High Voltage Charger Protocol

FEATURES

- USB Power Delivery (PD) Rev.3.0 Certified Provider
- Provides USB PD 5V, 9V, 12V Source Power Output
- USB Type-CTM Rev.1.2 Compliant Source
- Supports Qualcomm® Quick Charging 3.0/2.0(QC3.0/QC2.0)™ Protocol
- Supports HiSilicon® Fast Charge Protocol(FCP/SCP)
- Supports Samsung® Adaptive Fast Charging(AFC)
- Supports MediaTek® Pump Express Plus(PE+)
- Meets Battery Charging Specification BC 1.2 for DCP
- Supports USB DCP applying 2.7V on DP and DM line, output Current up to 2.4A for Apple® Device
- High Voltage and Safety Integration
- Overvoltage, Under-voltage, Overcurrent, Over-temperature Protection and VBUS Discharge
- Input Pin for Fast Shutdown Under Fault
- Internal N-channel HV MOSFET integration for best cost
- Overvoltage Protection on CC1, CC2, DP and DM
- Wide VIN Supply (4.25-16V)
- Supports NTC
- Low Quiescent Current when Unattached (Typical 20uA)
- Package: SSOP-16

APPLICATIONS

- Car charger
- USB Power Output Ports
- AC power Adapter for cellphone, notebook, tablet, VR box, UAV, robot Adapter

DESCRIPTION

The LT1008P is a low-cost USB Power Delivery Port Controller which is fully compliant to USB Power Delivery 3.0 version and Type-C revision 1.2 and BC 1.2 and other non BC1.2 standards like YD/T 1591-2009 Apple® & Samsung® Charging Spec, HiSilicon® Fast Charge Protocol, Qualcomm® Quick Charging™ 3.0/2.0.

The LT1008P monitors the CC pin to detect when a USB Type-C sink is attached, then it turn on VBUS and automatically detect whether a connected Device is USB PD 3.0 or Quick Charge 2.0/3.0 or FCP/SCP or AFC or PE+ Capable before enabling output voltage adjustment. If the Device not compliant to which description, it disables output voltage adjustment to ensure safe operation with legacy 5V. Protection features include overvoltage protection, undervoltage protection, overcurrent protection, over-temperature, overvoltage protection on CC1, CC2, DP and DM, and except overvoltage protection on CC1, CC2, DP, DM, system override to turn off VBUS and restart to detecting.

The LT1008P typically draws 20uA when no device is attached. Additional system power saving is achievable by using the Port Attachment Indicator (UFP) output to disable the power source when no device is attached.

The LT1008P is available in SSOP16 package.

Ordering Information

Part Number	Marking	Functional Specifications	Package
LT1008P2	LINTOP LT1008P2	5V/9V (MAX:18W)	SSOP16
LT1008P3	LINTOP LT1008P	5V/9V/12V (MAX:18W)	SSOP16

Marking:

1:LINTOP

2:LT1008P (Part Number)

3:XXXXXX(Lot Number)

Typical Application Schematic

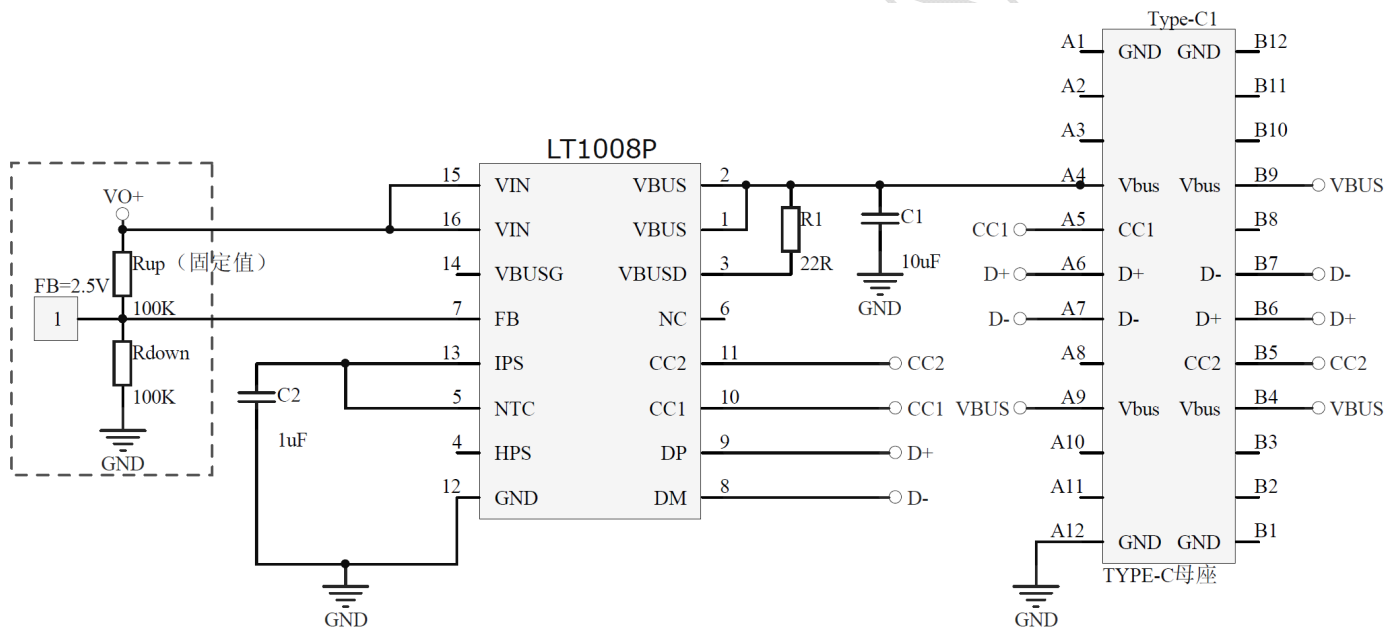


Figure 1.

PACKAGE REFERENCE

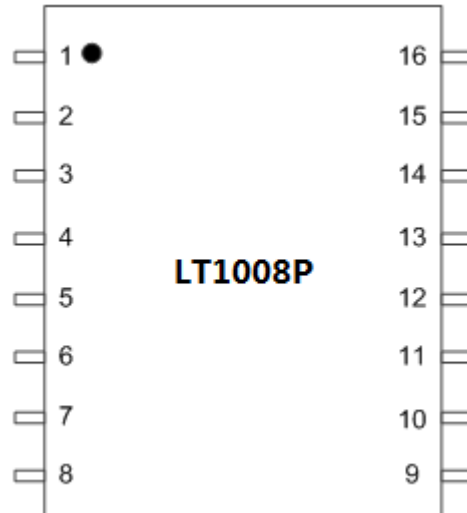


Figure 2.

PIN DESCRIPTION

NO.	NAME	DESCRIPTION
1	VBUS	The voltage monitor for VBUS line, which is the high-side power conductor
2	VBUS	The voltage monitor for VBUS line, which is the high-side power conductor
3	VBUSD	Open-drain output to discharge the system VBUS line through an external resistor
4	HPS	A five-state input used for selecting the maximum power that can be provided.
5	NTC	External shutdown control, can be configured for OTP by connecting an NTC resistor to GND
6	NC	---
7	FB	Current source/sink output for output voltage adjustment
8	DM	USB negative data line
9	DP	USB positive data line
10	CC1	Configuration channel interface pin to USB Type-C
11	CC2	Configuration channel interface pin to USB Type-C
12	GND	Power ground
13	IPS	Internal regulated power supply for PMU, need a bypass capacitor
14	VBUSG	High voltage open drain gate driver used to drive NMOS power switch, connected to the gate terminal
15	VIN	External voltage source
16	VIN	External voltage source

ABSOLUTE MAXIMUM RATINGS (1)

PARAMETER		MIN	MAX	UNIT
Voltage Range (To PGND)	V _{BUSG} , V _{BUS} , V _{IN} , V _{BUSD}	-0.3	16	V
	V(V _{BUSG})-V(V _{BUS})	-0.3	7	V
	Others	-0.3	6	V
Operating Junction Temperature	T _J	-40	150	°C
Storage Temperature Range	T _{STG}	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

ESD RATING

SYMBOL	PARAMETER	VALUE	UNIT
V _{ESD}	CC1/CC2/DP/DM	±8000	V
	Others	±2000	V
R _{θJA}	Junction-to-ambient thermal resistance	100	°C/W
R _{θJctop}	Junction-to-case(top) thermal resistance	36	°C/W
R _{θJB}	Junction-to-board thermal resistance	45	°C/W

RECOMMENDED OPERATING CONDICTIONS

PARAMETER	MIN	TYP	MAX	UNIT
V _{VIN}	Input Supply Voltage	4.5	15	V
R _{VBUSD}	Series Resistance	22	100	Ω
C _{IPS}	IPS Bypass Capacitance	0.1	2.2	μF
C _{VBUS}	Output Capacitance	2.2	10	μF
R _{FBUP}	Feedback Pull-up Resistor	100		KΩ
T _A	Operation Temperature Range	-40	85	°C

ELECTRICAL CHARACTERISTICS

Unless otherwise stated in a specific test condition the following Conditions apply: T_J = 25°C, 5V ≤ V_{VIN} ≤ 15V, C_{IPS} = 1Uf

PARAMETER	TEST CONDICTIONS	MIN	TYP	MAX	UNIT
Power Supply (VBUS, VIN)					
V _{VIN_TH}	VIN UVLO threshold	Rising edge		3.7	V
		Falling edge		3.4	
		Hysteresis		0.3	
V _{VBUS_TH}	VBUS UVLO threshold	Rising edge		4.45	V
		Falling edge		3.9	
		Hysteresis		0.55	
I _{VIN}	Quiescent Current	VIN=5V, CCx open		20	uA
I _{SUPP}	Operating current while sink attached	VIN=5V, VBUS=5V		2	mA

Voltage Protection (VBUS)						
V _{FOVP}	Fast OVP threshold, always enabled	Ref to target voltage		+20%		V
V _{SOVP}	Slow OVP threshold	Ref to target voltage		+15%		V
V _{SUVP}	VBUS UVP threshold	Ref to target voltage		-22%		V
IPS						
V _{IPS}	Output voltage	$0 \leq I_{IPS} \leq I_{IPS_EXT}$		3.65		V
I _{IPS_EXT}	External load allowed				5	mA
Discharge (VBUSD)						
Fast discharge	ON state (linear)	Internal switch		6		Ω
Slow discharge	ON state (saturation)	Internal resistor		1000		Ω
Switch MOSFET						
RDSON				12		m Ω
NMOS gate driver (VBUSG, GDNS)						
IN VBUSG ON	Sourcing current	$0V \leq V_{GDNS} \leq 25V,$ $0V \leq V_{VBUSG} - V_{GDNS} \leq 6V$		10		μA
V VBUSG ON	Sourcing voltage (V VBUSG - VGDNS)	$0V \leq V_{GDNS} \leq 25V, I_{VBUSG\ ON} \leq 4\mu A$	4		6	V
Transmitter (CC1, CC2)						
RTX	Output resistance	During transmission		50		Ω
VTXHI	Transmit HIGH			1.25		V
VTXLO	Transmit LOW		-75		75	mV
tUI	Bit unit interval			3.3		us
tBMC	Rise/fall time of BMC	Rload=5.1k, Cload=1nF	300		600	ns
Receiver (CC1, CC2)						
VRXHI	Receive HIGH		800	840	885	mV
VRXLO	Receive LOW		485	525	570	
IRP_SRC	CC1/CC2 Broadcasting current	3A DFP mode, $0 \leq V_{CCX} \leq 2.5V$	304	330	356	μA
		1.5A DFP mode, $0 \leq V_{CCX} \leq 1.5V$	166	180	194	μA
VOVP_CC	CC1/CC2 OVP threshold				5.5	V
OCP (ISEN, VBUS)						
VITRIP	Shunt voltage when OCP tripped	Ref to Power Capability(pd)		+30%		A
OTP (internal)						
TJ1	Die temperature	Temperature rising edge	125	135	145	$^{\circ}C$
		Hysteresis		20		$^{\circ}C$
NTC						
VOTPDET	External OTP based on NTC	Temperature rising edge		0.3		VIPS
		Hysteresis		0.1		VIPS

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HVDCP interface (DP, DM)						
VDAT(REF)	Date Detect Voltage		0.25	0.325	0.4	V
VSEL(REF)	Output voltage selection reference		1.8	2	2.2	V
TGLITCH(DP)HIGH	DP High Glitch Filter Time		1	1.25	1.5	s
TGLITCH(DM)LOW	DM Low Glitch Filter Time			1		ms
TGLITCH(V)CHANGE	Output Voltage Glitch Filter Time		20	40	60	ms
TGLITCH(CONT)CHANGE	Continuous Mode Glitch Filter Time		100	150	200	us
RDAT(LKG)	DP		300	500	800	KΩ
RDM(DWN)	D- Pull-Down Resistance		14.25	19.53	24.5	KΩ
RON(N1)	SwitchSW1 on-resistance			40	100	Ω
VTH(PD)	Data Line Capacitance		0.25	0.325	0.4	V
TDPD	Output Device Connection Detection threshold		120	160	200	ms
ΔIT(UP)	Output Device connection Detection Glitch Filter Time	RIREF=100KΩ		2		uA
ΔIT(DO)	Up Current Step	RIREF=100KΩ		2		uA
VOVP_DPDM	Down Current Step				5.5	V
Apple 2.4A Mode						
VDAT(2.7V)	D+/D- line output voltage		2.57	2.7	2.84	V
RDAT(2.7V)	D+/D- line output Impedance			15		KΩ
FCP Mode						
VTX-VOH	D- FCP TX Valid High			2.7		V
VTX-VOL	D- FCP TX Valid Low				0.3	V
VRX-VIH	D- FCP RX Valid High			1.2		V
VRX-VIL	D- FCP RX Valid High			0.9		V
Trise	FCP Pulse Rise Time	10% - 90%			2.5	us
Tfall	FCP Pulse Fall Time	90% - 10%			2.5	us



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Function Description

Power Data Object Advertise

The power advertised to PD Sinks is always 18 W. The LT1008P advertises 5V/3A, 9V/2A, 12V/1.5A&5V/3A, 9V/2A.

Discharge Function

In order to ensure the voltage change or abnormal protection VBUS voltage satisfies the requirement of PD in the prescriptive time, LT1008P supports Discharge Function. The external series resistor between VBUS and VBUS is need if enabled this function, which recommended value for 22Ω (VBUS 10uf capacitance in parallel case, it is recommended to use 1/4 W or higher power encapsulated resistance).

FB

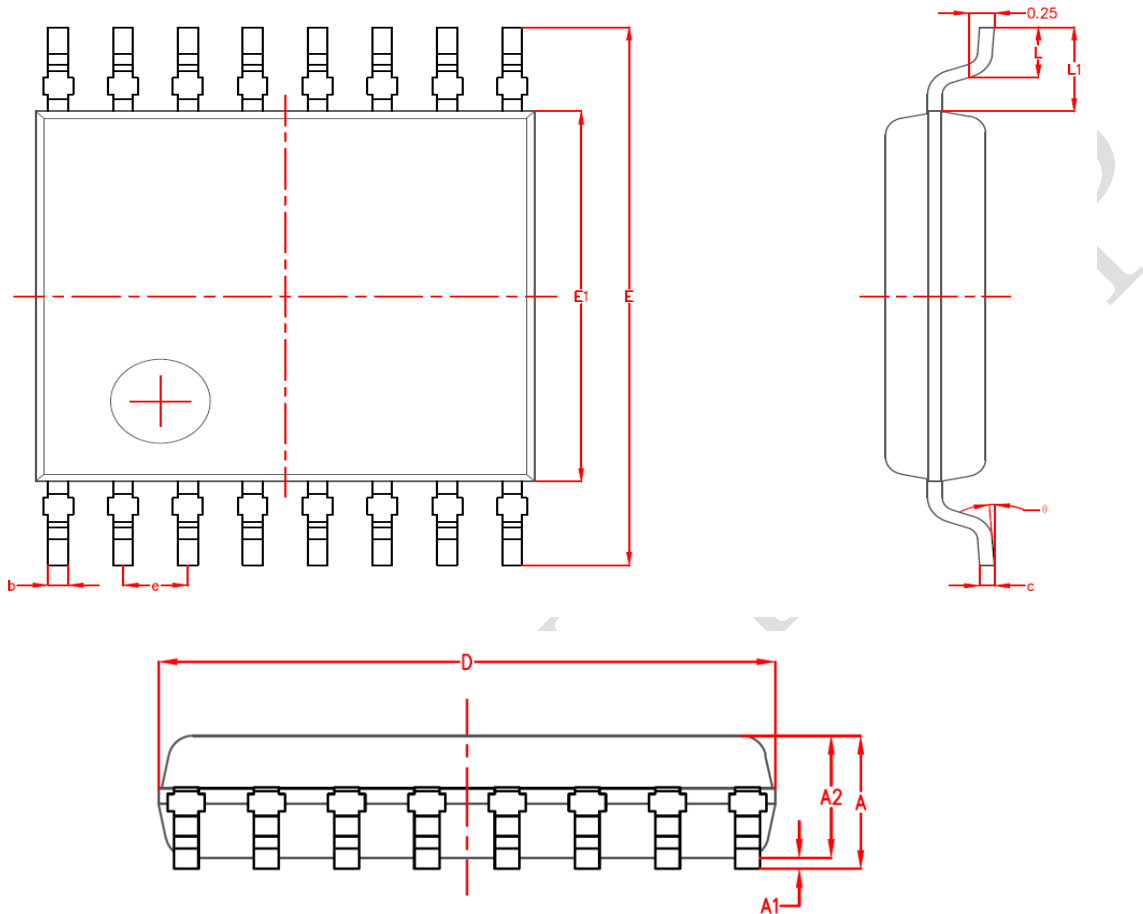
LT1008P through FB Source or Sink current to achieve voltage regulation for 2uA steps, thus FB need access to the system voltage feedback point and the pull up resistance value must be 100KΩ.

NTC

NTC can be used to closed the fast charge when pull it GND or when which voltage is lowed to 0.3 IPS can be used for NTC to closed Fast charge

PACKAGING INFORMATION

SSOP-16 PACKAGE OUTLINE DIMENSION



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	-	1.09	1.19
A1	0.02	-	0.15
A2	0.95	1.00	1.05
b	0.14	0.22	0.30
c	0.08	0.13	0.18
D	4.90	5.00	5.10
E	6.20	6.40	6.60
E1	4.30	4.40	4.50
e	0.65BSC		
L	0.5	0.60	0.70
L1	1.05BSC		
theta	0°	4°	8°